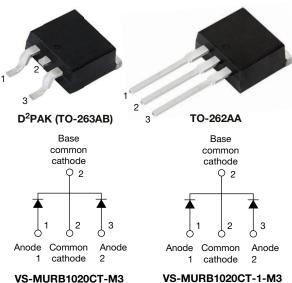
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VS-MURB1020CT-M3, VS-MURB1020CT-1-M3

Vishay Semiconductors

Ultrafast Rectifier, 2 x 5 A FRED Pt[®]



PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 x 5 A			
V _R	200 V			
V _F at I _F	0.87 V			
t _{rr}	25 ns			
T _J max.	175 °C			
Package	D ² PAK (TO-263AB), TO-262AA			
Circuit configuration	Common cathode			

FEATURES

- Ultrafast recovery time
- · Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance. ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage		V _{RRM}		200	V		
Average restified forward surrent	per leg	1		5			
Average rectified forward current	total device	IF(AV)	Rated V _R , T _C = 149 °C	10			
Non-repetitive peak surge current per leg		I _{FSM}		50	A		
Peak repetitive forward current per leg		I _{FM}	Rated V_R , square wave, 20 kHz, T_C = 149 °C	10			
Operating junction and storage tem	peratures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS			MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-			
		I _F = 5 A, T _J = 25 °C	-	0.99	1.08	UNITS 		
	V	I _F = 5 A, T _J = 125 °C	-	0.87	0.99	- V		
Forward voltage	V _F	I _F = 10 A, T _J = 25 °C	-	1.12	1.25			
		I _F = 10 A, T _J = 125 °C	-	1.02	.12 1.25			
		$V_{R} = V_{R}$ rated	-	-	10			
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μΑ		
Junction capacitance	CT	V _R = 200 V	-	8	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50$	0 A/µs, V _R = 30 V	-	-	35			
Reverse recovery time	+	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ V}$		-	-	25			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	24	-	ns		
		T _J = 125 °C		-	35	-			
Peak recovery current	1	T _J = 25 °C	l _F = 5 A dl _F /dt = 200 A/µs	-	3.3	-	А		
Feak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 160 \text{V}$	-	5.0	-	A		
	0	T _J = 25 °C	VR = 100 V	-	33	-	nC		
Reverse recovery charge	Q _{rr}	T _J = 125 °C]	-	76	-	10		

THERMAL - MECHANIC	CAL SPEC	IFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	-	5	
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Maisht			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking davias		Case style D ² PAK (TO-263AB)	MURB1020CT			
Marking device		Case style TO-262		MURB1	020CT-1	

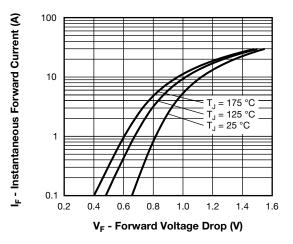


Fig. 1 - Typical Forward Voltage Drop Characteristics

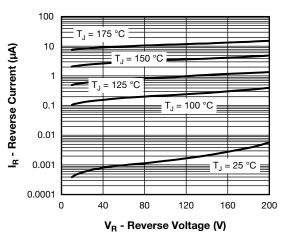


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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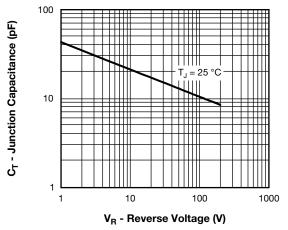


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

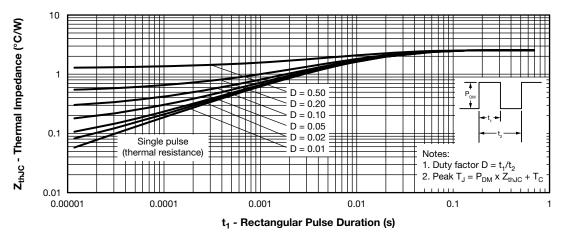
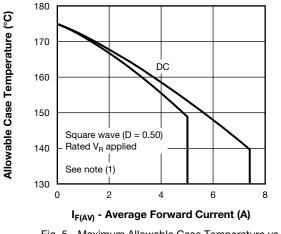
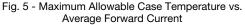
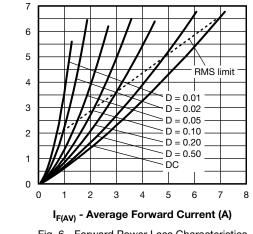


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

Average Power Loss (W)

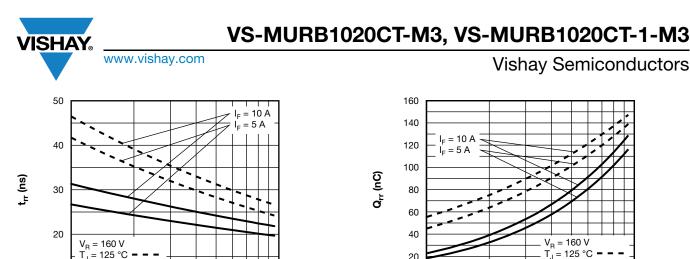




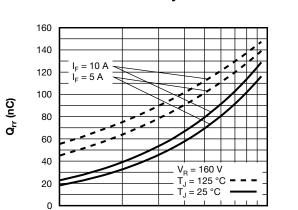


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T_J 1000 dl_F/dt (A/µs) Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt



100

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1000



Note

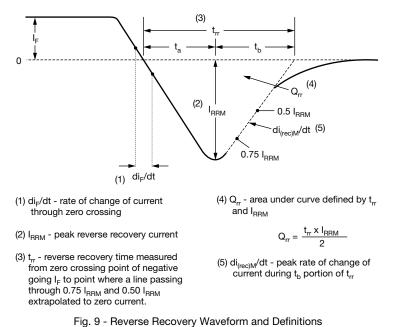
10

100

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

= 25 °C

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

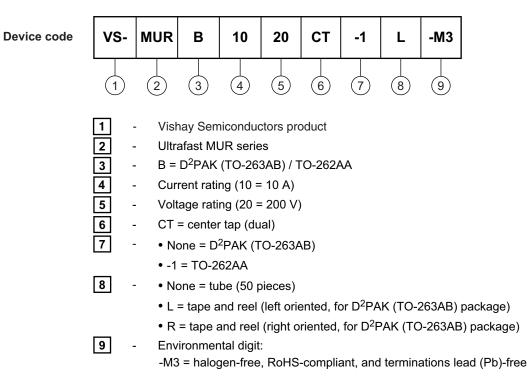




VS-MURB1020CT-M3, VS-MURB1020CT-1-M3

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ORDERING INFORMATION TABLE



	LINKS TO RELATED DO	CUMENTS
Dimensions —	D ² PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions	TO-262AA	www.vishay.com/doc?96165
Dout marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444
Part marking information —	TO-262AA	www.vishay.com/doc?95443
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?96424

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIMETERS		INC	HES	NOTES	
STMBOL	MIN. MAX.		MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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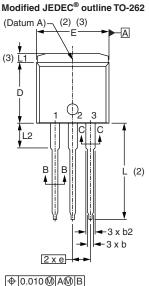
Outline Dimensions

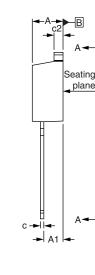


Vishay Semiconductors

TO-262AA

DIMENSIONS in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

CYMPOL	MILLIN	IETERS	INC	HES	NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis and the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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